BLF8G20LS-210V; BLF8G20LS-210GV

Power LDMOS transistor

Rev. 1 — 25 February 2014

Objective data sheet

1. Product profile

1.1 General description

210 W LDMOS power transistor with improved video bandwidth for base station applications at frequencies from 1805 MHz to 1990 MHz.

Table 1. Typical performance

Typical RF performance at $T_{case} = 25 \ ^{\circ}C$ in a common source class-AB production test circuit.

Test signal	f	I _{Dq}	V_{DS}	P _{L(AV)}	Gp	η_D	ACPR _{5M}
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
2-carrier W-CDMA	1805 to 1880	1600	28	50	18.5	25	-30 [1]

 Test signal: 3GPP test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF per carrier; 5 MHz carrier spacing.

1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Decoupling leads to enable improved video bandwidth (<tbd>)
- Designed for broadband operation (1805 MHz to 1990 MHz)
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

 RF power amplifiers for W-CDMA base stations and multi carrier applications in the 1805 MHz to 1990 MHz frequency range



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2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
BLF8G20)LS-210V (SOT1244B)		
1	drain		
2	gate	- 4 1 5	6 7 → 1 → 4,5
3	source [1		
4	decoupling lead	3	2 1
5	decoupling lead		aaa-003619
6	n.c.		
7	n.c.	6 2 7	
BLF8G20)LS-210GV (SOT1244C)		
1	drain	4 4 5	
2	gate		6 7 → 1 → 4,5
3	source [1		
4	decoupling lead		2 I I 3
5	decoupling lead		aaa-003619
6	n.c.	- 6 2 7 3	
7	n.c.		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	ackage					
	Name	Description	Version				
BLF8G20LS-210V	-	earless flanged ceramic package; 6 leads	SOT1244B				
BLF8G20LS-210GV	-	earless flanged ceramic package; 6 leads	SOT1244C				

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage			-	65	V
V_{GS}	gate-source voltage			-0.5	+13	V
T _{stg}	storage temperature			-65	+150	°C
Tj	junction temperature		<u>[1]</u>	-	225	°C

[1] Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

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5. Thermal characteristics

Table 5.	Thermal characteristics			
Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	$T_{case} = 80 \ ^{\circ}C; P_{L} = 50 \ W$	<tbd></tbd>	K/W

6. Characteristics

Table 6. DC characteristics

 $T_i = 25 \ ^{\circ}C$ unless otherwise specified.

.,						
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 3 mA	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V_{DS} = 10 V; I_{D} = 300 mA	1.5	1.9	2.3	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 28 \text{ V}; I_D = 1600 \text{ mA}$	1.6	2	2.4	V
I _{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V	-	-	2.8	μA
I _{DSX}	drain cut-off current	$\label{eq:VGS} \begin{array}{l} V_{GS} = V_{GS(th)} + 3.75 \; V; \\ V_{DS} = 10 \; V \end{array}$	-	53	-	A
I _{GSS}	gate leakage current	V_{GS} = 11 V; V_{DS} = 0 V	-	-	280	nA
g _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 153 mA	-	<tbd></tbd>	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ I _D = 10.5 A	-	0.05	-	Ω

Table 7. RF characteristics

Test signal: 2-carrier W-CDMA, 3GPP test model 1 with 64 DPCH; PAR = 8.4 dB at 0.01 % probability on the CCDF; $f_1 = 1807.5$ MHz; $f_2 = 1812.5$ MHz; $f_3 = 1872.5$ MHz; $f_4 = 1877.5$ MHz; RF performance at $V_{DS} = 28$ V; $I_{Dq} = 1600$ mA; $T_{case} = 25$ °C; unless otherwise specified; in a water cooled AB test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	$P_{L(AV)} = 50 \text{ W}$	<tbd></tbd>	18.5	-	dB
η_D	drain efficiency	$P_{L(AV)} = 50 \text{ W}$	<tbd></tbd>	25	-	%
RL _{in}	input return loss	$P_{L(AV)} = 50 \text{ W}$	-	-10	<tbd></tbd>	dB
$ACPR_{5M}$	adjacent channel power ratio (5 MHz)	$P_{L(AV)} = 50 \text{ W}$	-	-30	<tbd></tbd>	dBc

7. Test information

7.1 Ruggedness in class-AB operation

The BLF8G20LS-210V and BLF8G20LS-210GV are capable of withstanding a load mismatch corresponding to VSWR = <tbd> : 1 through all phases under the following conditions: $V_{DS} = 28$ V; $I_{Dq} = 1600$ mA; $P_L = 210$ W (CW); f = 1800 MHz.

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8. Package outline

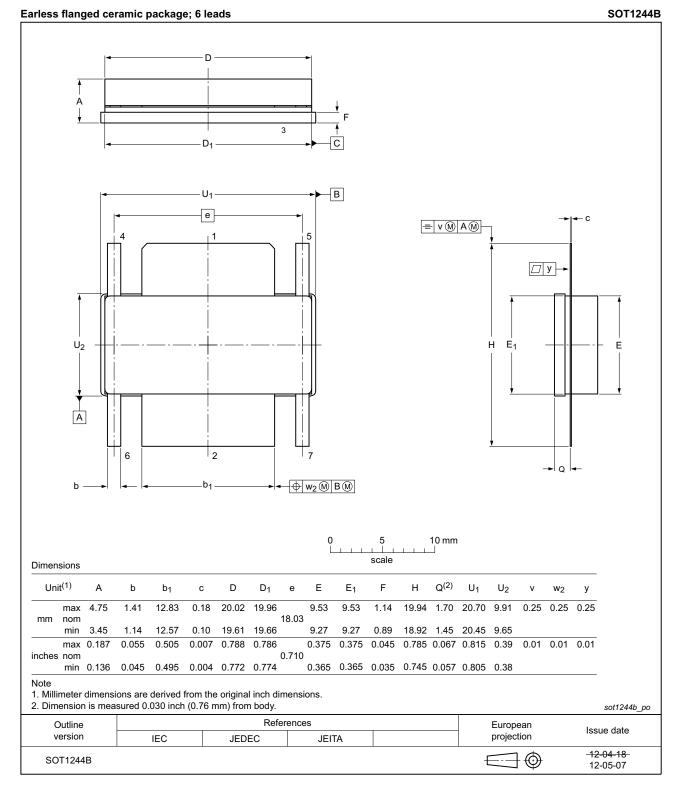


Fig 1. Package outline SOT1244B

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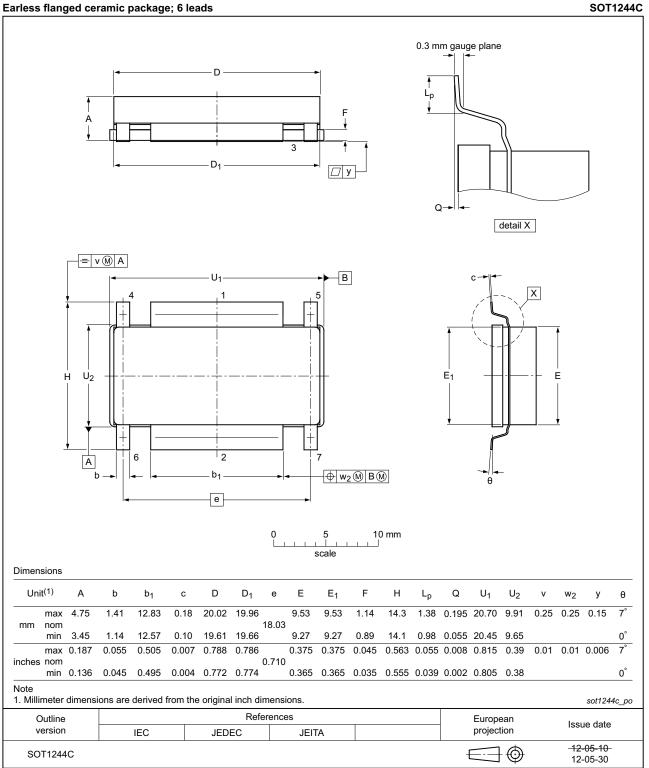


Fig 2. Package outline SOT1244C

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

10. Abbreviations

Table 8.	Abbreviations
Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal Oxide Semiconductor
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 9. Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF8G20LS-210V_20LS-210GV v.1	20140225	Objective data sheet	-	-

12. Legal information

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Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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